

FIG. 1B

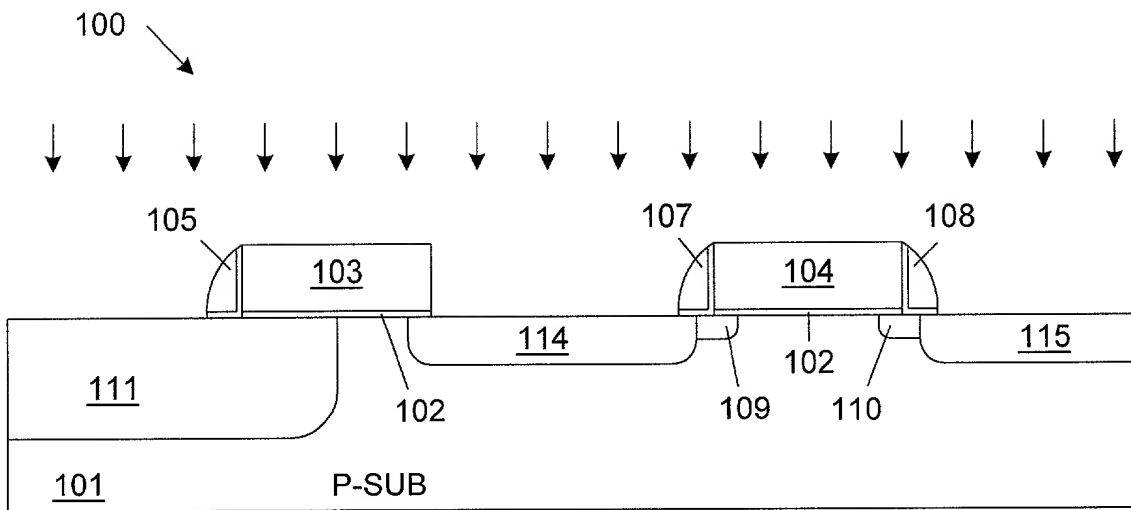


FIG. 1C

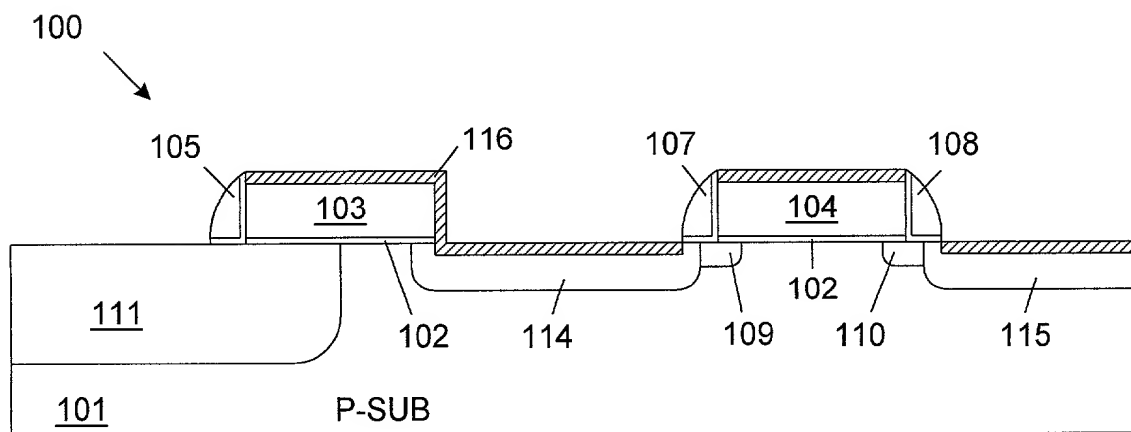


FIG. 1D

A cross-sectional view of a semiconductor device. The substrate is labeled **P-SUB** and **201**. Two active regions are formed on the substrate, each containing a central layer (204 and 205) and a surrounding layer (206 and 207). The active regions are separated by a gap. The device is covered by a top layer (208) and a bottom layer (209). The top layer is labeled **200**. The bottom layer is labeled **210**, **211**, and **212**. The central layers are labeled **202** and **203**. The surrounding layers are labeled **206** and **207**. The top layer is labeled **208**. The bottom layer is labeled **209**. The device is covered by a top layer (208) and a bottom layer (209). The top layer is labeled **200**. The bottom layer is labeled **210**, **211**, and **212**. The central layers are labeled **202** and **203**. The surrounding layers are labeled **206** and **207**. The top layer is labeled **208**. The bottom layer is labeled **209**.

FIG. 2C

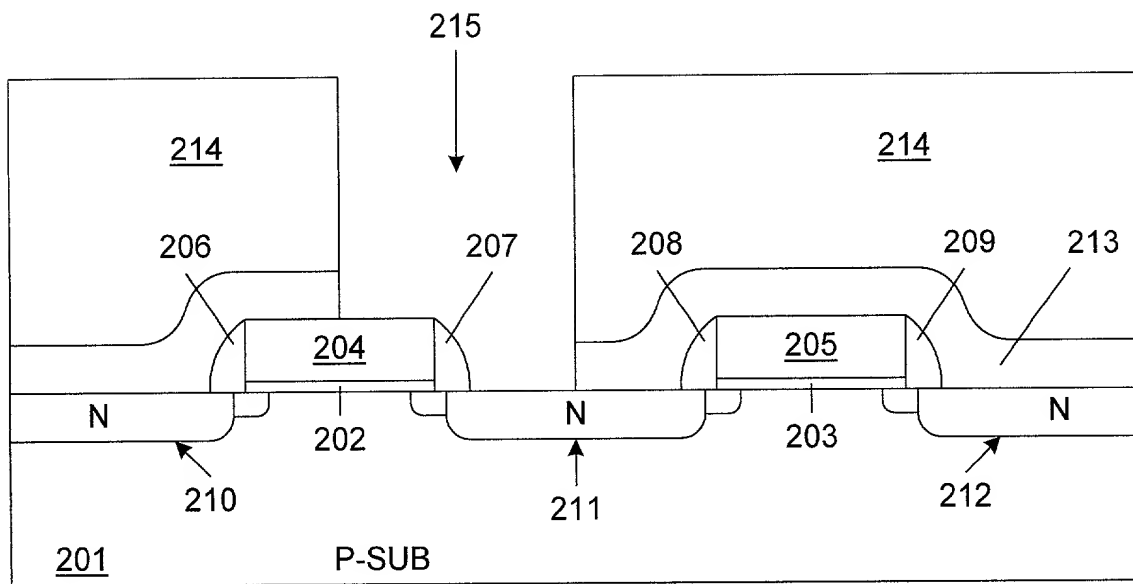


FIG. 2D

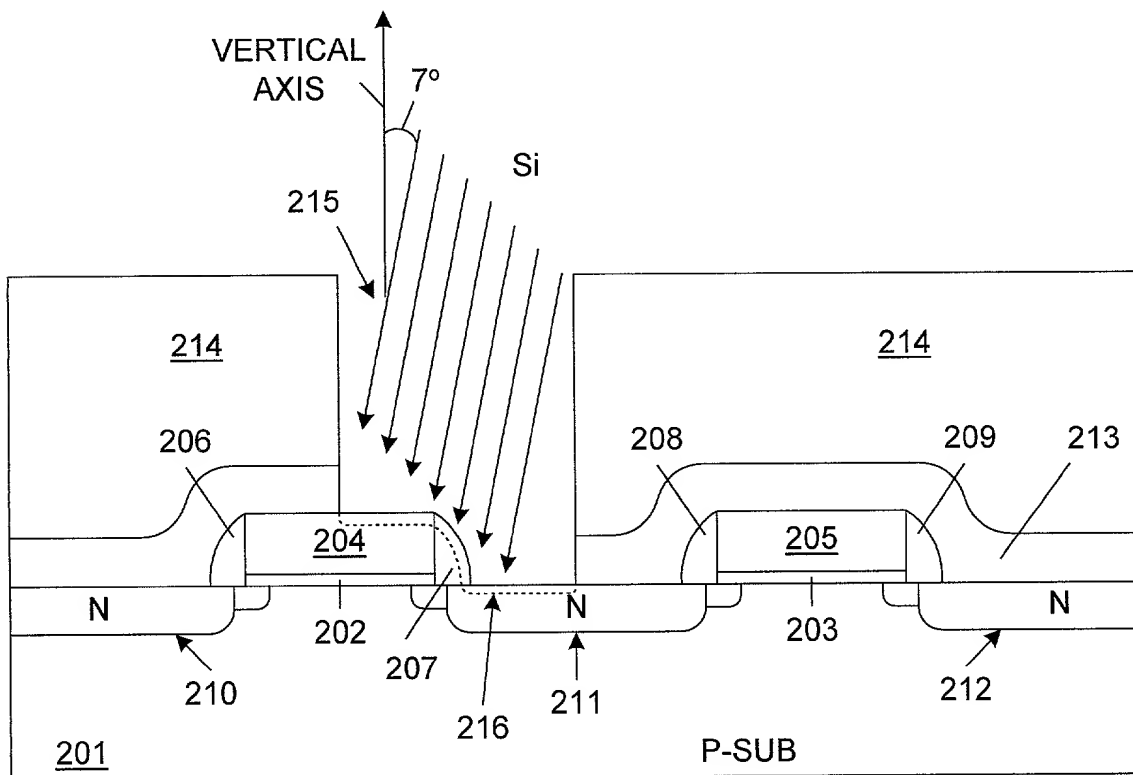


FIG. 2E

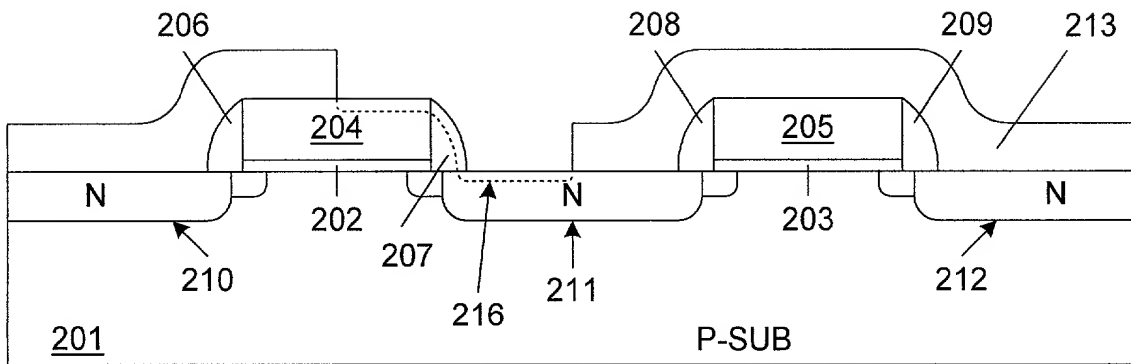


FIG. 2F

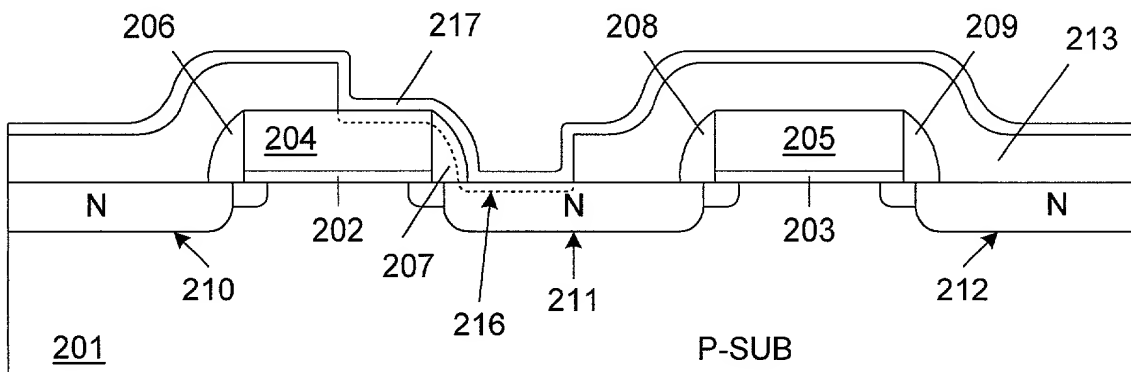


FIG. 2G

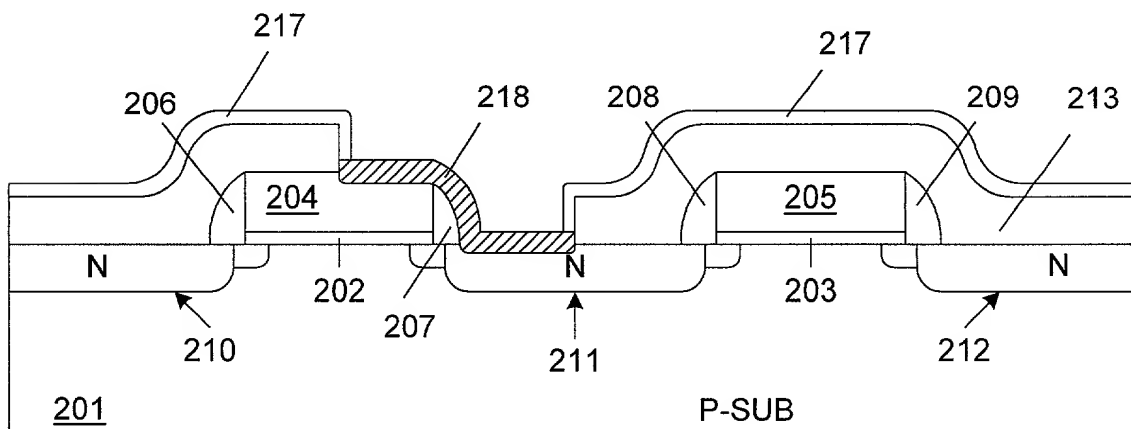


FIG. 2H

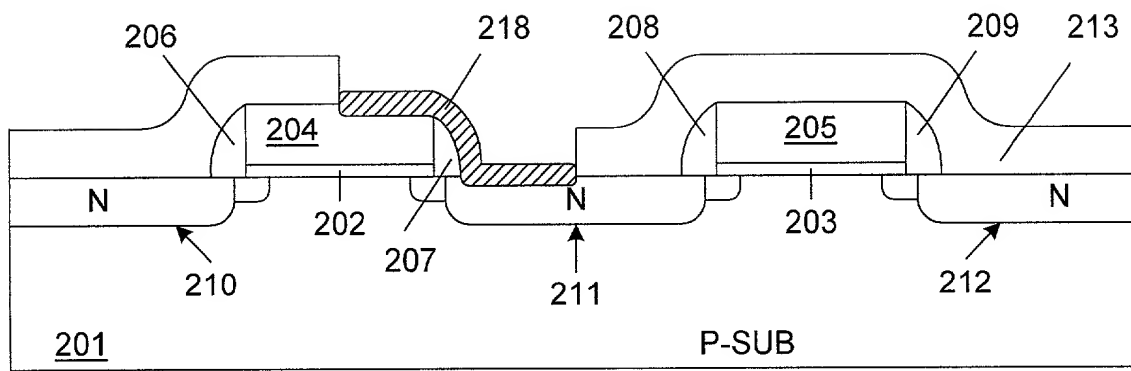


FIG. 2I